



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOT-23 封装半导体晶体管/SOT-23 Plastic-Encapsulate Transistors

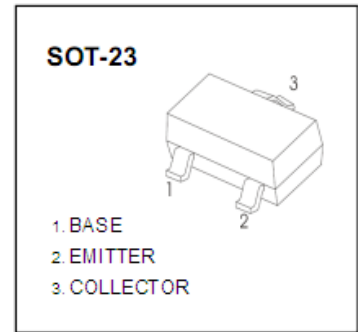
## 2SC2712 ( NPN )

### 特点/Features :

噪声低，放大线性好;

### 用途/Applications :

用于一般放大。



### 极限参数/Absolute maximum ratings(Ta=25°C)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	$V_{CB0}$	60	V
集电极-发射极电压/Collector-Emitter Voltage	$V_{CE0}$	50	V
发射极-基极电压/Emitter-Base Voltage	$V_{EB0}$	5	V
集电极连续电流/Collector Current Continuous	$I_C$	0.15	A
集电极耗散功率/Collector Power Dissipation	$P_C$	0.15	W
结温/Junction Temperature	$T_j$	150	°C
储存温度/Storage Temperature	$T_{stg}$	-55~150	°C

### 电性能参数/Electrical characteristics (Ta=25°C)

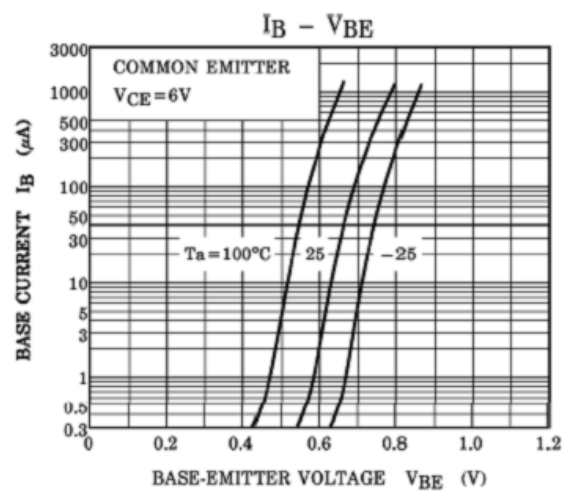
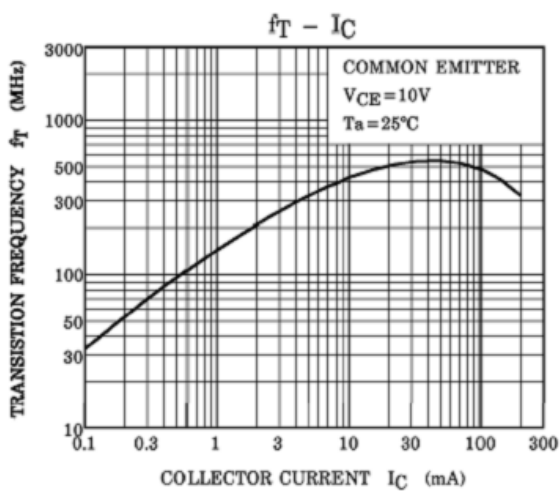
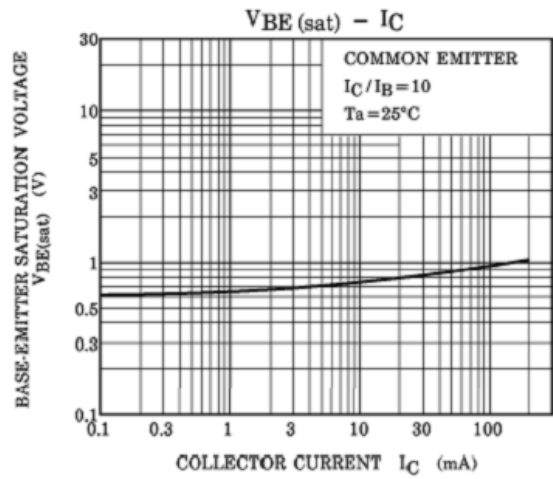
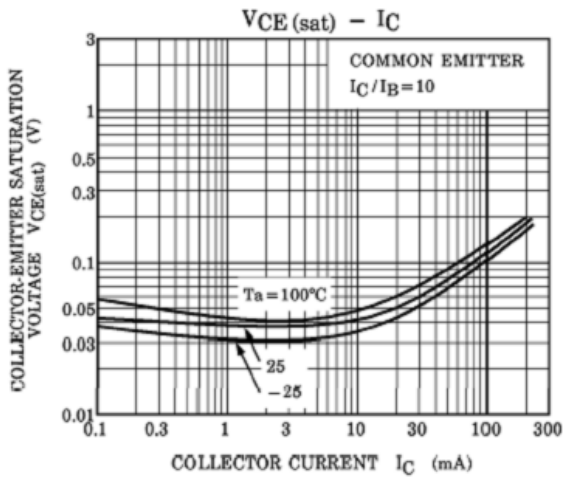
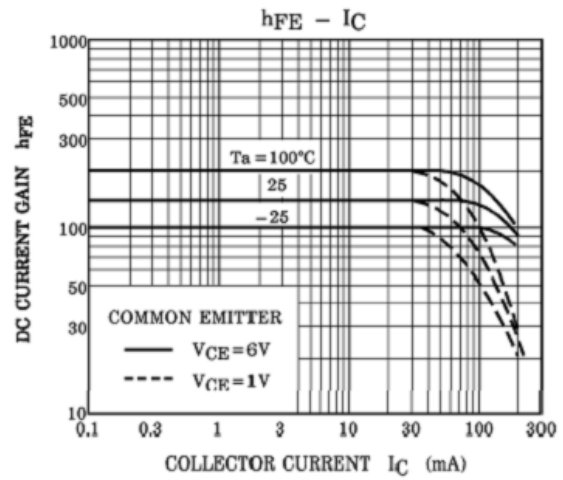
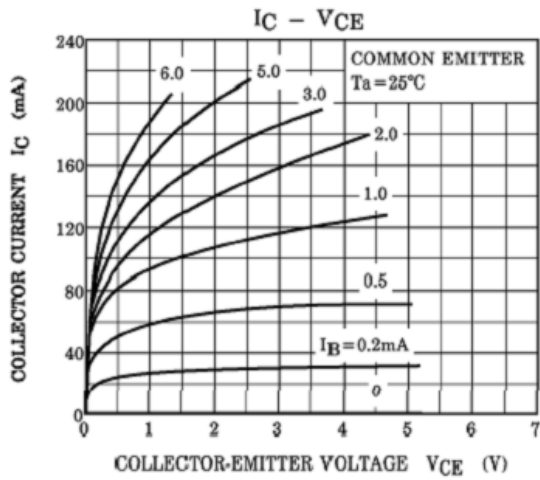
参数	符号	测试条件	最小值	典型值	最大值	单位
集电极-基极击穿电压	$V_{BR(CB0)}$	$I_C=100\ \mu A, I_E=0$	60			V
集电极-发射极击穿电压	$V_{BR(CE0)}$	$I_C=1mA, I_B=0$	50			V
发射极-基极击穿电压	$V_{BR(EB0)}$	$I_E=100\ \mu A, I_C=0$	5			V
集电极截止电流	$I_{CB0}$	$V_{CB}=60V, I_E=0$			0.1	$\mu A$
发射极截止电流	$I_{EB0}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
直流电流增益	$h_{FE}$	$V_{CE}=6V, I_C=2mA$	70		700	
集电极-发射极饱和压降	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$		0.1	0.25	V
特征频率	$f_T$	$V_{CE}=10V, I_C=1mA$	80			MHz
输出电容	$C_{ob}$	$V_{CB}=10\ V, I_E=0, f=1MHz$		2.0	3.5	pF
噪声系数	NF	$V_{CE}=6V, I_C=0.1mA, f=1kHz,$ $R_g=10K\ \Omega$		1.0	10	dB

### Marking And $h_{FE}$ 分档/Classification of $h_{FE}$

档位/Rank	0	Y	GR	BL
范围/Range	70~140	120~240	200~400	350~700
印章/Marking	L0	LY	LG	LL



### 典型特性曲线图/Typical Characteristics





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